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PCN #190 Notification Date: June 19, 2020

Product / Process Change Notice

Parts Affected:

Chip process CP375, N-channel MOSFETs, wafers and bare die.

Extent of Change:

The CP375 wafer process has been discontinued and is being replaced with the CP406 wafer process. See Figures 1 and 2 for details.

Reason for Change:

The CP375 wafer process has been replaced in order to enhance manufacturing process controls and device performance. This change will help ensure an undisrupted supply of product.

Effect of Change:

The CP406 wafer process meets all electrical specifications of the individual devices listed on the following page.

Qualification:

P/N: CP406 Chip Process Package: TO-220

N	lo.	Test	Conditions (Reference standards are in bold)	Qty	Pass/Fail	Test Results	
1		Device Life Tests					
	А	High Temperature Gate Bias (HTGB)	T=150°C, t = 1000 hours 100% V_GS Negative Bias JESD22-A108	77	Pass	77/77	
	В	High Temperature Gate Bias (HTGB)	T=150°C, t = 1000 hours 100% V_GS Positive Bias JESD22-A108	77	Pass	77/77	
	С	High Temperature Reverse Bias (HTRB)	T=150°C, t = 1000 hours 100% V_DS JESD22-A108	77	Pass	77/77	

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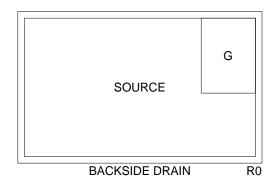
Effective Date of Change:

Existing inventory of chip process CP375 will be shipped until depleted.

Sample Availability:

Please contact your salesperson or manufacturer's representative for samples.

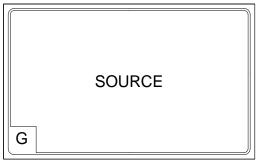
Figure 1: CP375 Chip Geometry (Discontinued)



Wafer Diameter: 8 inch
Die Size: 62 x 38 mils
Die Thickness: 7.5 mils
Bond Pad Size (Gate): 13.7 x 18.8 mils
Bond Pad Size (Source): 55 x 30 mils
Topside Metal: Al (40,000Å)

Backside Metal: Ti/Ni/Ag (1,000Å/3,000Å/10,000Å)

Figure 2: CP406 Chip Geometry



BACKSIDE DRAIN

Wafer Diameter: 8 inch

Die Size: 63.8 X 38.9 mils
Die Thickness: 5.5 mils
Bond Pad Size (Gate): 7.1 x 7.1 mils
Bond Pad Size (Source): 60.4 x 35.6 mils
Topside Metal: Al-Cu (40,000Å)

Backside Metal: Ti/Ni/Ag (1,000Å/3,000Å/10,000Å)

Part Numbers Affected:

CWDM3011N	CP375-CWDM3011N-CT
	CP375-CWDM3011N-WN

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As per JEDEC standard JESD46, Customer Notification of Product/Process Changes by Solid-State Suppliers, a lack of acknowledgement of a PCN within thirty (30) days constitutes acceptance of the change.

The undersigned acknowledges and accepts Central Semiconductor's Product/Process Change Notification (PCN).

Company Name:	
Address:	
Printed Name:	
Title:	
Signature:	
Date:	

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